

电子设计技术

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EDN评论

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高峰视点

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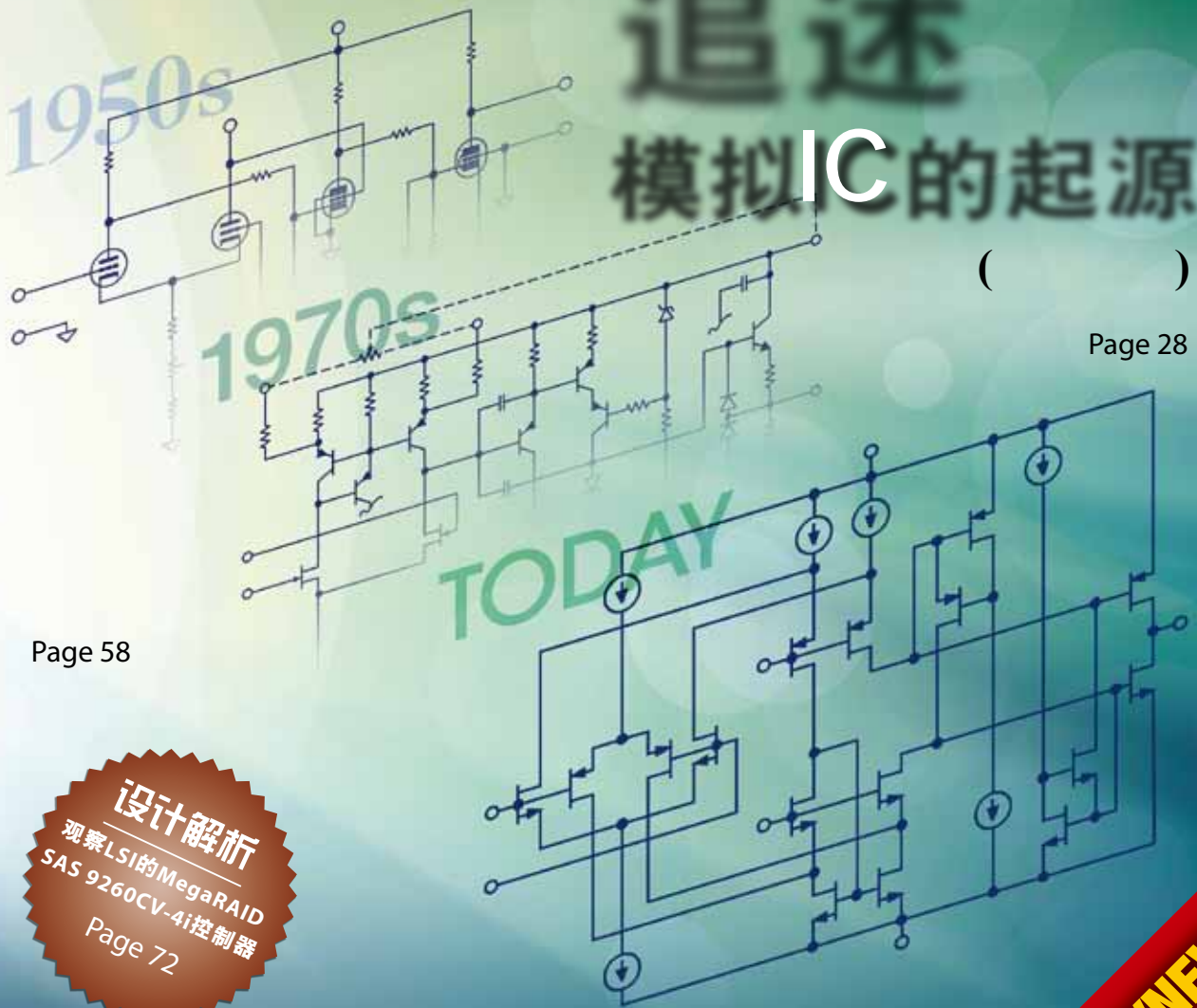
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设计策略

132kHz CCM

PSR


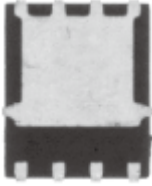





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设计解析
观察LSI的MegaRAID
SAS 9260CV-4i控制器
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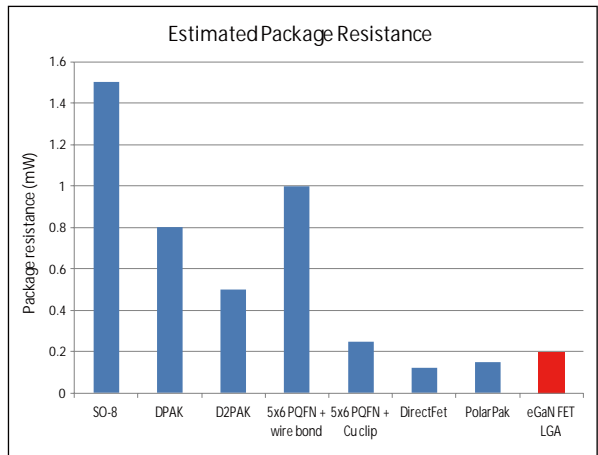
100V 7mW max	 4.1 x 1.6 mm	 5 x 6 mm PQFN		
100V 30mW max	 1.7 x 1.1 mm		 4.8 x 3.9 mm DirectFET	
200V 100mW max	 1.7 x 0.9 mm		 6.3 x 5 mm DirectFET	 5 x 6 mm PolarPAK


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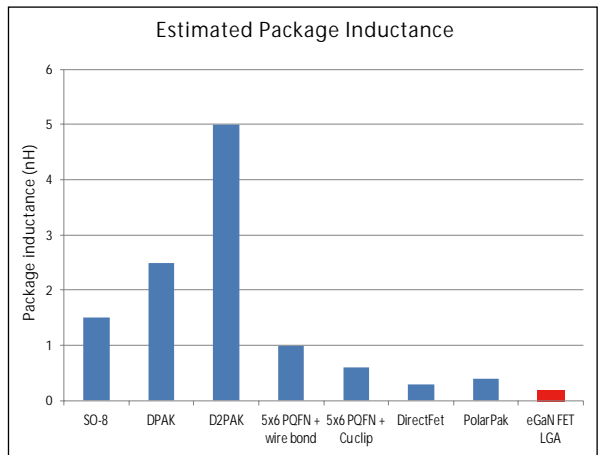

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 3. <http://www.vishay.com/company/press/releases/2005/051214mosfets/>
 4. <http://www.greatwallsemi.com/AppNotes/BGAMounting.pdf>
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